



Peak gate current ( $t_p=20\mu s$ , $T_j=125$ )	$I_{GM}$	12	A
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	22	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	1.3	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

<b>Symbol</b>	<b>Test Condition</b>	<b>Value</b>	<b>Unit</b>
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**JCT16110IS**

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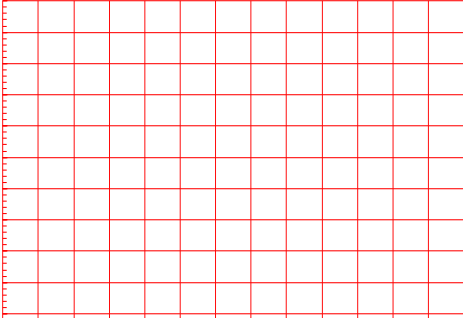
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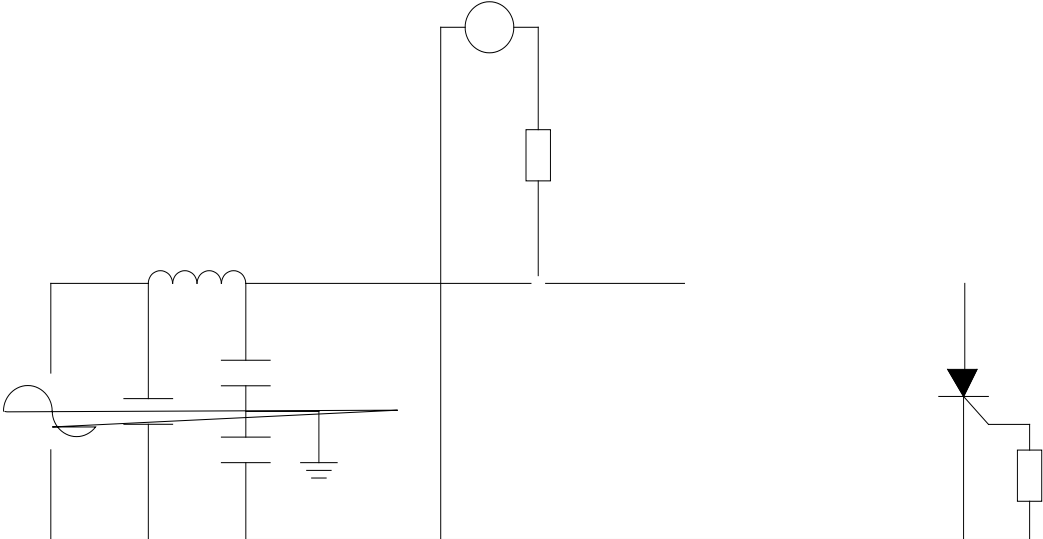
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**FIG.1:** Maximum power dissipation versus RMS on-state current



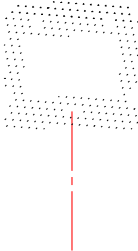
**FIG.2:** RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.






PACKAGE MECHANICAL DATA



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